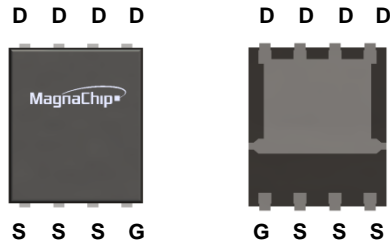


### General Description

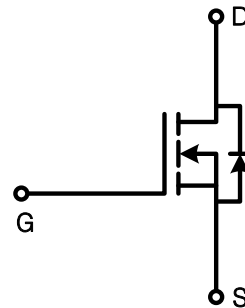
The MDU10N180 uses advanced MagnaChip's MOSFET Technology, which provides high performance in on-state resistance, fast switching performance and excellent quality. MDU10N180 is suitable device for Synchronous Rectification For Server and general purpose applications.

### Features

- $V_{DS} = 100V$
- $I_D = 40 A @ V_{GS} = 10V$
- Very low on-resistance  $R_{DS(ON)}$   
 $< 18.0 m\Omega @ V_{GS} = 10V$   
 $< 23.0 m\Omega @ V_{GS} = 4.5V$
- 100% UIL Tested
- 100% Rg Tested



PDFN56



### Absolute Maximum Ratings ( $T_J = 25^\circ C$ )

Characteristics		Symbol	Rating	Unit
Drain-Source Voltage		$V_{DSS}$	100	V
Gate-Source Voltage		$V_{GSS}$	$\pm 20$	V
Continuous Drain Current <sup>(1)</sup>	$T_C = 25^\circ C$ (Silicon Limited)	$I_D$	48.1	A
	$T_C = 25^\circ C$ (Package Limited)		40	
	$T_C = 100^\circ C$ (Silicon Limited)		30.4	
	$T_A = 25^\circ C$		12.4	
Pulsed Drain Current <sup>(3)</sup>		$I_{DM}$	160	
Power Dissipation	$T_C = 25^\circ C$	$P_D$	83.3	W
	$T_C = 100^\circ C$		33.3	
	$T_A = 25^\circ C$		5.5	
Single Pulse Avalanche Energy <sup>(2)</sup>		$E_{AS}$	50	mJ
Junction and Storage Temperature Range		$T_J, T_{stg}$	-55~150	$^\circ C$

### Thermal Characteristics

Characteristics	Symbol	Rating	Unit
Thermal Resistance, Junction-to-Ambient <sup>(1)</sup>	$R_{\theta JA}$	22.7	$^\circ C/W$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.5	

## Ordering Information

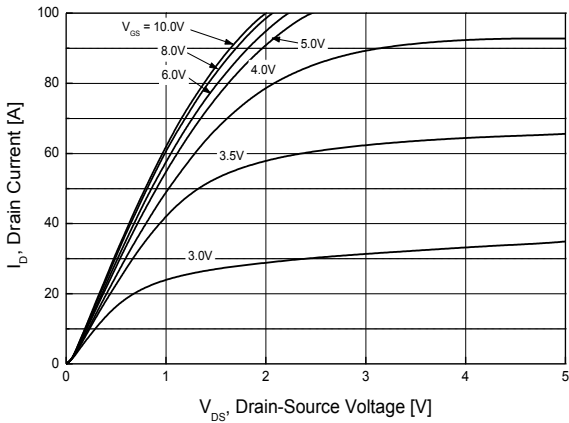
Part Number	Temp. Range	Package	Packing	RoHS Status
MDU10N180RH	-55~150°C	PDFN56	Tape & Reel	Halogen Free

## Electrical Characteristics (T<sub>J</sub> =25°C)

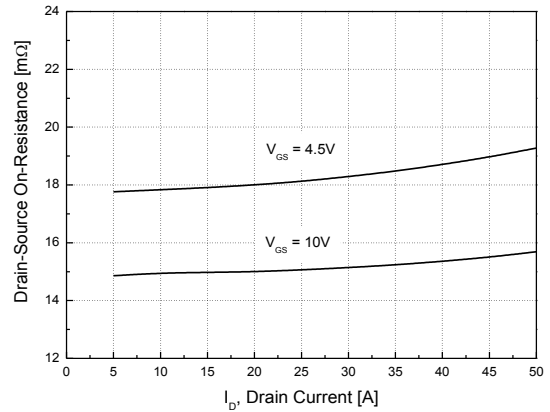
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
<b>Static Characteristics</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	I <sub>D</sub> = 250μA, V <sub>GS</sub> = 0V	100	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	1.0	1.5	2.0	
Drain Cut-Off Current	I <sub>DSS</sub>	V <sub>DS</sub> = 100V, V <sub>GS</sub> = 0V	-	-	1.0	μA
Gate Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V	-	-	±100	nA
Drain-Source ON Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A	-	15	18	mΩ
		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 20A	-	18	23	
Forward Transconductance	g <sub>fs</sub>	V <sub>DS</sub> = 10V, I <sub>D</sub> = 20A	-	45	-	S
<b>Dynamic Characteristics</b>						
Total Gate Charge	Q <sub>g(10V)</sub>	V <sub>DD</sub> = 50V, I <sub>D</sub> = 20A, V <sub>GS</sub> = 10V	-	30.8	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	6.0	-	
Gate-Drain Charge	Q <sub>gd</sub>		-	5.1	-	
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 40V, V <sub>GS</sub> = 0V, f = 1.0MHz	-	1,995	-	pF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	18	-	
Output Capacitance	C <sub>oss</sub>		-	253	-	
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>GS</sub> = 10V, V <sub>DD</sub> = 50V, I <sub>D</sub> = 20A, R <sub>G</sub> = 3Ω,	-	8.0	-	ns
Rise Time	t <sub>r</sub>		-	10.5	-	
Turn-Off Delay Time	t <sub>d(off)</sub>		-	26.3	-	
Fall Time	t <sub>f</sub>		-	7.4	-	
Gate Resistance	R <sub>g</sub>	f=1.0 MHz	-	1.0	-	Ω
<b>Drain-Source Body Diode Characteristics</b>						
Source-Drain Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = 20A, V <sub>GS</sub> = 0V	-	0.8	1.2	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 20A, di/dt = 100A/μs	-	54	-	ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>		-	120	-	nC

Note :

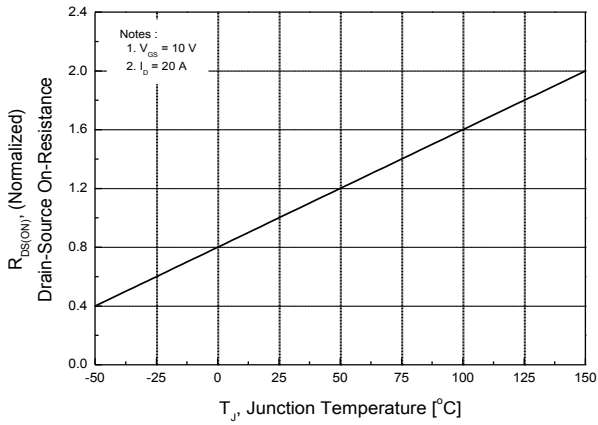
- Surface mounted FR-4 board by JEDEC (jesd51-7). Continuous current at T<sub>C</sub>=25°C is silicon limited
- E<sub>AS</sub> is tested at starting T<sub>J</sub> = 25°C, L = 1.0mH, I<sub>AS</sub> = 10A, V<sub>GS</sub> = 10V.
- Pulse width limited by T<sub>Jmax</sub>



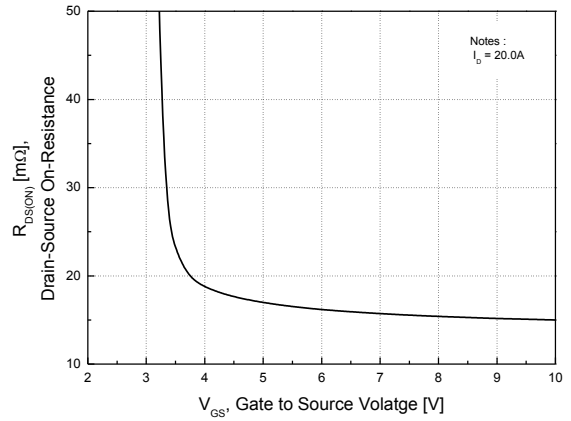
**Fig.1 On-Region Characteristics**



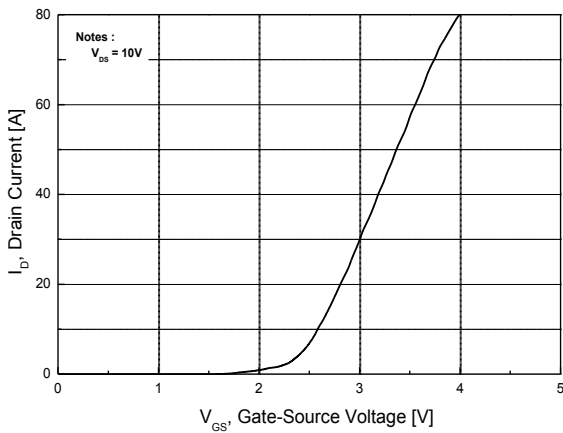
**Fig.2 On-Resistance Variation with Drain Current and Gate Voltage**



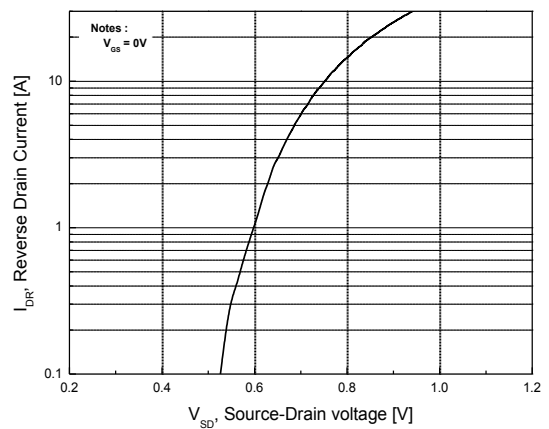
**Fig.3 On-Resistance Variation with Temperature**



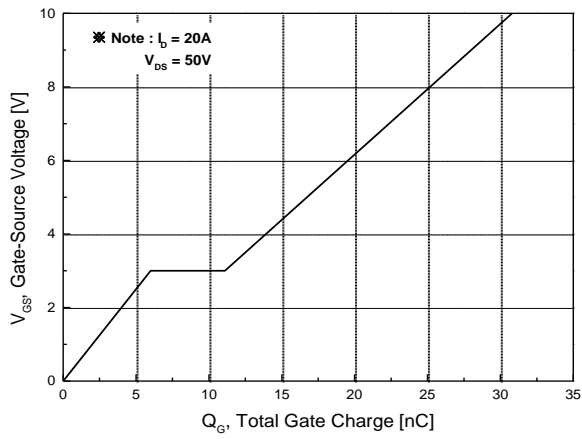
**Fig.4 On-Resistance Variation with Gate to Source Voltage**



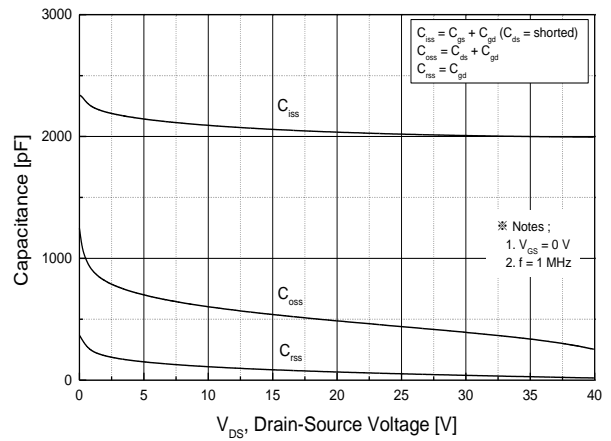
**Fig.5 Transfer Characteristics**



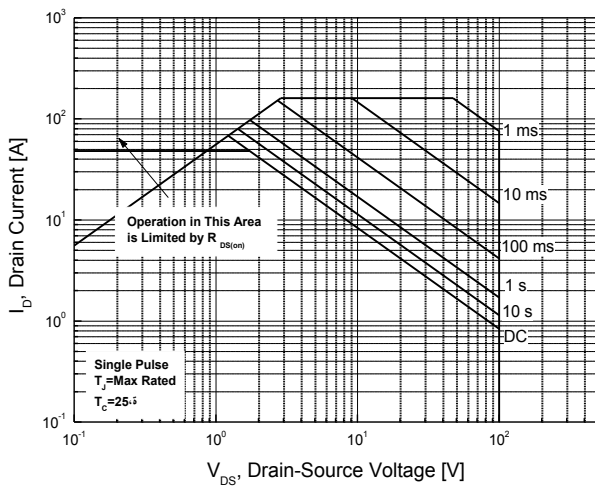
**Fig.6 Body Diode Forward Voltage Variation with Source Current and Temperature**



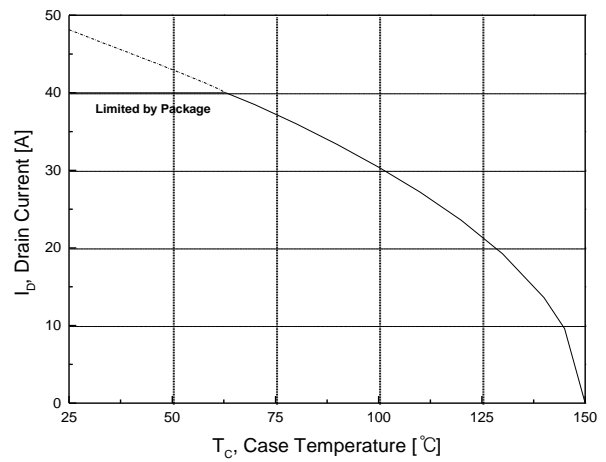
**Fig.7 Gate Charge Characteristics**



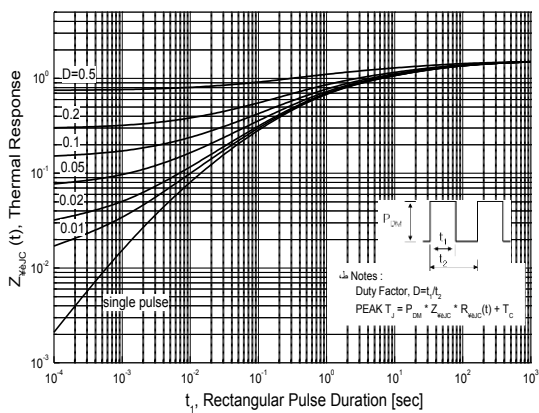
**Fig.8 Capacitance Characteristics**



**Fig.9 Maximum Safe Operating Area**



**Fig.10 Maximum Drain Current vs. Case Temperature**



**Fig.11 Transient Thermal Response Curve**



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